FAIRCHILD SEMICONDUCTOR™

March 1994
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74ABT125
Quad Buffer with 3-STATE Outputs

General Description

The ABT125 contains four independent non-inverting buffers with 3-STATE outputs.

Features

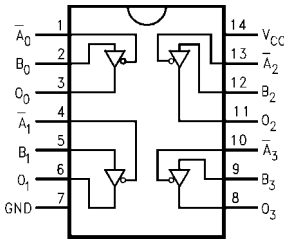
- Non-inverting buffers
- Output sink capability of 64 mA, source capability of 32 mA
- Guaranteed latchup protection
- High impedance glitch free bus loading during entire power up and power down cycle
- Nondestructive hot insertion capability
- Disable time less than enable time to avoid bus contention

Ordering Code:

Order Number	Package Number	Package Description
74ABT125CSC	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150" Narrow Body
74ABT125CSJ	M14D	14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
74ABT125CMTC	MTC14	14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153,4.4mm Wide

Device also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering code.

Connection Diagram



Pin Descriptions

Pin Names	Descriptions
$\overline{A}_n$, B_n	Inputs
O_n	Outputs

Function Table

Inputs		Output
A_n	B_n	O_n
L	L	L
L	H	H
H	X	Z

H = HIGH Voltage Level
L = LOW Voltage Level
Z = HIGH Impedance
X = Immaterial

Absolute Maximum Ratings(Note 1)

Storage Temperature	−65°C to +150°C
Ambient Temperature under Bias	−55°C to +125°C
Junction Temperature under Bias	−55°C to +150°C
V_{CC} Pin Potential to	
Ground Pin	−0.5V to +7.0V
Input Voltage (Note 2)	−0.5V to +7.0V
Input Current (Note 2)	−30 mA to +5.0 mA
Voltage Applied to Any Output	
in the Disabled or	
Power-Off State	−0.5V to 5.5V
in the HIGH State	−0.5V to V_{CC}
Current Applied to Output	
in LOW State (Max)	twice the rated I_{OL} (mA)
DC Latchup Source Current	
(Across Comm Operating Range)	−300 mA
Over Voltage Latchup (I/O)	10V

Recommended Operating Conditions

Free Air Ambient Temperature	−40°C to +85°C
Supply Voltage	+4.5V to +5.5V
Minimum Input Edge Rate (ΔV/Δt)	
Data Input	50 mV/ns
Enable Input	20 mV/ns

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

DC Electrical Characteristics

Symbol	Parameter		Min	Typ	Max	Units	V_{CC}	Conditions
V_{IH}	Input HIGH Voltage					V		Recognized HIGH Signal
V_{IL}	Input LOW Voltage				0.8	V		Recognized LOW Signal
V_{CD}	Input Clamp Diode Voltage				−1.2	V	Min	I_{IN} = −18 mA
V_{OH}	Output HIGH Voltage		2.5			V	Min	I_{OH} = −3 mA
			2.0			V	Min	I_{OH} = −32 mA
V_{OL}	Output LOW Voltage				0.55	V	Min	I_{OL} = 64 mA
I_{IH}	Input HIGH Current				1	μA	Max	V_{IN} = 2.7V (Note 3)
					1			V_{IN} = V_{CC}
I_{BVI}	Input HIGH Current Breakdown Test				7	μA	Max	V_{IN} = 7.0V
I_{IL}	Input LOW Current				−1	μA	Max	V_{IN} = 0.5V (Note 3)
					−1			V_{IN} = 0.0V
V_{ID}	Input Leakage Test					V	0.0	I_{ID} = 1.9 μA, All Other Pin Grounded
I_{OZH}	Output Leakage Current				10	μA	0–5.5V	V_{OUT} = 2.7V; $\overline{OE}_n$ = 2.0V
I_{OZL}	Output Leakage Current				−10	μA	0–5.5V	V_{OUT} = 0.5V; $\overline{OE}_n$ = 2.0V
I_{OS}	Output Short-Circuit Current				−275	mA	Max	V_{OUT} = 0.0V
I_{CEX}	Output HIGH Leakage Current				50	μA	Max	V_{OUT} = V_{CC}
I_{ZZ}	Bus Drainage Test				100	μA	0.0	V_{OUT} = 5.5V; All Others GND
I_{CCH}	Power Supply Current				50	μA	Max	All Outputs HIGH
I_{CCL}	Power Supply Current				15	mA	Max	All Outputs LOW
I_{CCZ}	Power Supply Current				50	μA	Max	$\overline{OE}_n$ = V_{CC};
								All Others at V_{CC} or Ground
I_{CCT}	Additional I_{CC} /Input	Outputs Enabled			1.5	mA	Max	V_I = V_{CC} − 2.1V
		Outputs 3-STATE			1.5	mA		Enable Input V_I = V_{CC} − 2.1V
		Outputs 3-STATE			50	μA		Data Input V_I = V_{CC} − 2.1V
								All Others at V_{CC} or Ground
I_{CCD}	Dynamic I_{CC}	No Load				mA/		Outputs Open
	(Note 3)				0.1	MHz	Max	$\overline{OE}_n$ = GND, (Note 4)
								One Bit Toggling, 50% Duty Cycle

Note 3: Guaranteed, but not tested.

Note 4: For 8 bits toggling, I_{CCD} < 0.8 mA/MHz.

AC Electrical Characteristics

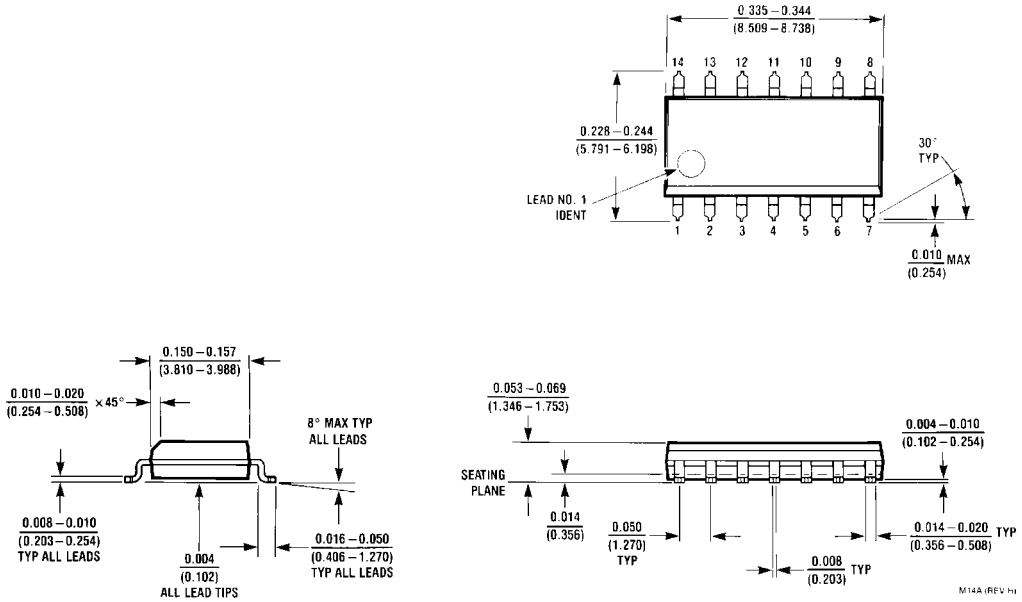
Symbol	Parameter	$T_A = +25°C$, $V_{CC} = +5V$, $C_L = 50$ pF			$T_A = -40°C$ to $+85°C$, $V_{CC} = 4.5V–5.5V$, $C_L = 50$ pF		Units
		Min	Typ	Max	Min	Max	
t_{PLH}	Propagation Delay	1.0		4.6	1.0	4.6	ns
t_{PHL}	Data to Outputs	1.0		4.9	1.0	4.9	
t_{PZH}	Output Enable	1.0		5.1	1.0	5.1	ns
t_{PZL}	Time	1.0		6.8	1.0	6.8	
t_{PHZ}	Output Disable	1.0		6.2	1.0	6.2	ns
t_{PLZ}	Time	1.0		5.5	1.0	5.5	

Capacitance

Symbol	Parameter	Typ	Units	Conditions $T_A = 25°C$
C_{IN}	Input Capacitance	5.0	pF	$V_{CC} = 0V$
C_{OUT} (Note 5)	Output Capacitance	9.0	pF	$V_{CC} = 5.0V$

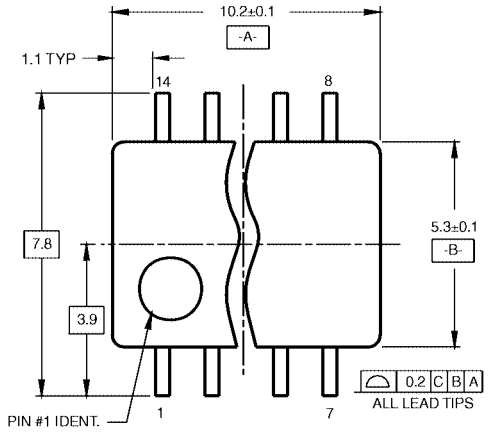
Note 5: C_{OUT} is measured at frequency f = 1 MHz, per MIL-STD-883, Method 3012.

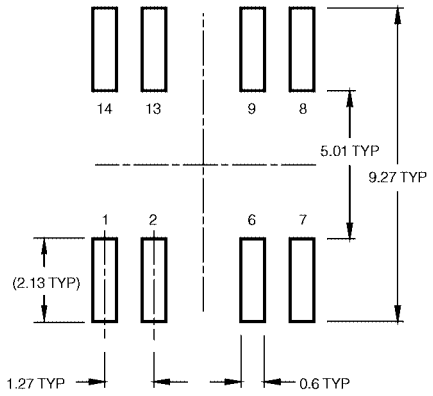
Physical Dimensions inches (millimeters) unless otherwise noted



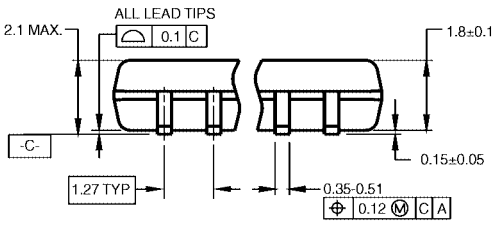
14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-013, 0.300" Wide Body
Package Number M14A

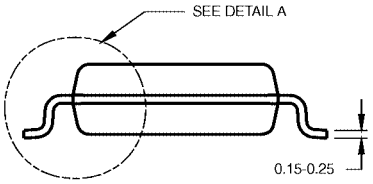
Physical Dimensions inches (millimeters) unless otherwise noted (Continued)





LAND PATTERN RECOMMENDATION





DIMENSIONS ARE IN MILLIMETERS

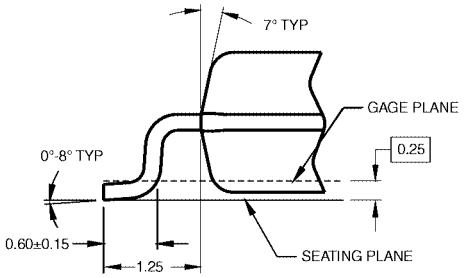
NOTES:

A. CONFORMS TO EIAJ EDR-7320 REGISTRATION, ESTABLISHED IN DECEMBER, 1998.

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

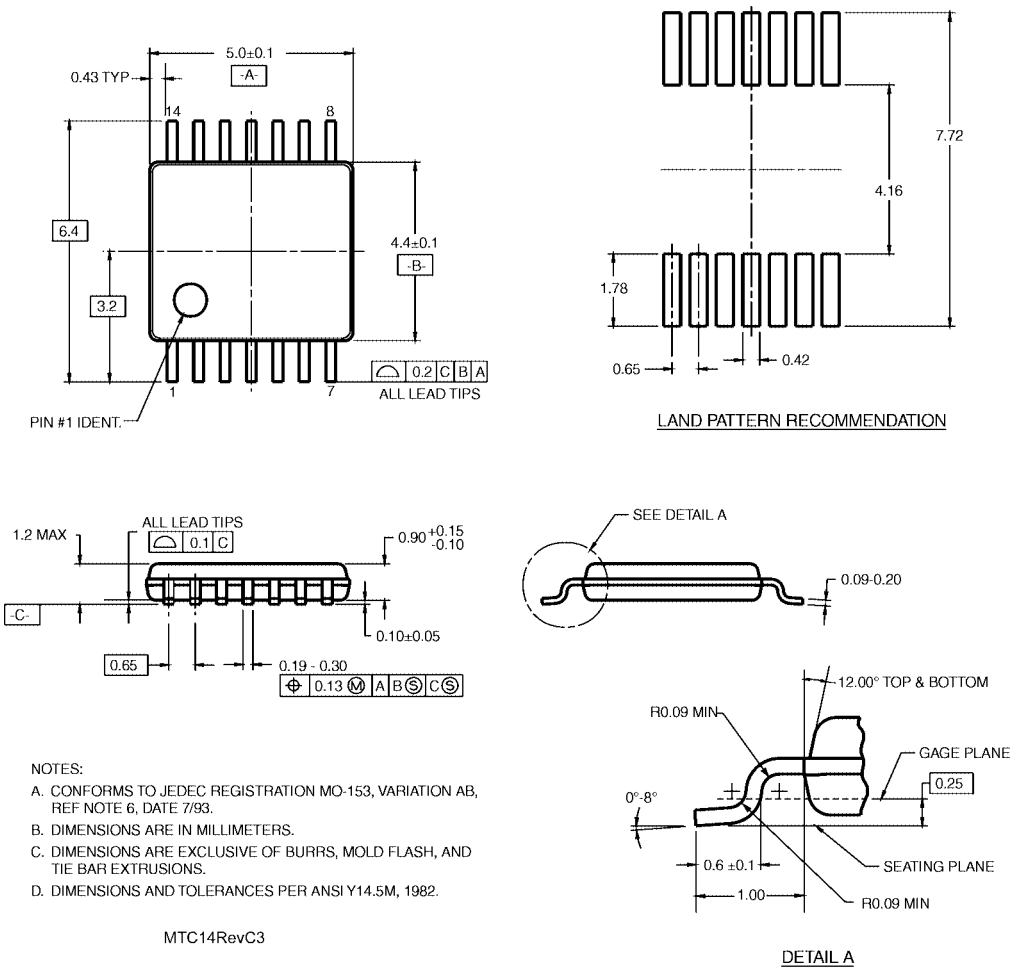
M14DRevB1



DETAIL A

14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
Package Number M14D

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



NOTES:

A. CONFORMS TO JEDEC REGISTRATION MO-153, VARIATION AB, REF NOTE 6, DATE 7/93.

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

D. DIMENSIONS AND TOLERANCES PER ANSI Y14.5M, 1982.

MTC14RevC3

14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
Package Number MTC14